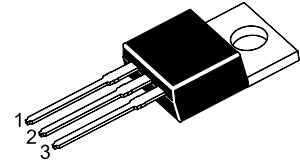


13007

NPN Silicon Transistor

for high voltage, high-speed power switching application



1.Base 2.Collector 3.Emitter
TO-220 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	700	V
Collector Emitter Voltage	V_{CEO}	400	V
Emitter Base Voltage	V_{EBO}	9	V
Collector Current	I_C	8	A
Total Power Dissipation ($T_a = 25^\circ\text{C}$)	P_{tot}	2	W
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	P_{tot}	80	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ A}$	h_{FE}	8	40	-
Collector Base Cutoff Current at $V_{CB} = 700\text{ V}$	I_{CBO}	-	1	mA
Emitter Base Cutoff Current at $V_{EB} = 9\text{ V}$	I_{EBO}	-	1	mA
Collector Base Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CBO}$	700	-	V
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	400	-	V
Emitter Base Breakdown Voltage at $I_E = 1\text{ mA}$	$V_{(BR)EBO}$	9	-	V
Collector Emitter Saturation Voltage at $I_C = 5\text{ A}$, $I_B = 1\text{ A}$	$V_{CE(sat)}$	-	2	V
Base Emitter Saturation Voltage at $I_C = 5\text{ A}$, $I_B = 1\text{ A}$	$V_{BE(sat)}$	-	1.6	V
Transition Frequency at $V_{CE} = 10\text{ V}$, $I_C = 0.5\text{ A}$	f_T	4	-	MHz

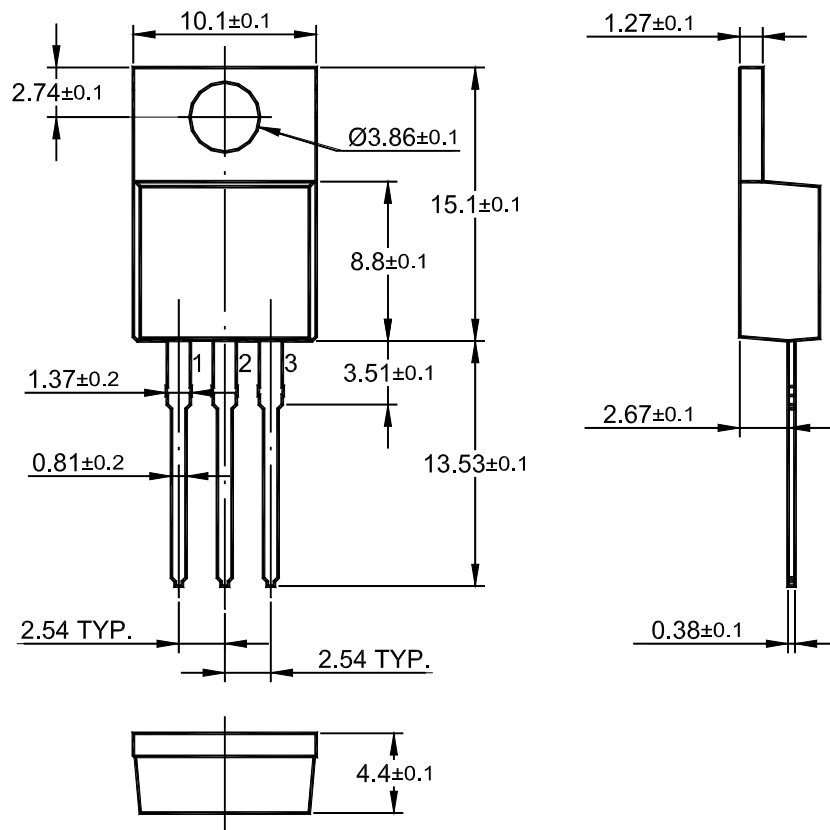
TOP DYNAMIC



ISO14001 : 2004
Certificate No. 121505007
ISO 9001 : 2008
Certificate No. 50114012
OHSAS 18001 : 2007
Certificate No. 0513150808
IECQ QC 080000
Certificate No. ECU1800714M2

Dated : 17/09/2016 Rev: 01

TO-220 PACKAGE OUTLINE



Dimensions in mm